Journal of Crystal Growth 132 (1993) 621–625
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Abe, Y., see Haga 132 (1993) 575
Aidun, D.K., see Shen 132 (1993) 250
Aidun, D.K., see Shen 132 (1993) 351
Ananth, R., see Lee 132 (1993) 226
Arai, Y., see Ono 132 (1993) 297
Arita, M., N. Suzuki and I. Nishida, Smoke particles of ytterbium and its oxides 132 (1993) 71
Armstrong, J.V., see Sun 132 (1993) 592
Atherton, L.J., see Brandon 132 (1993) 261

Ballman, A.A., see Cheng 132 (1993) 280
Bangert, U., A.J. Harvey, V.A. Wilkinson, C. Dieker, J.M. Jowett, A.D. Smith, S.D. Perrin and C.J. Gibbins, Evidence for strain relaxation via composition fluctuations in strained quaternary/quaternary and quaternary/ternary multiple quantum well structures 132 (1993) 231
Basmaji, P., see Lubyshev 132 (1993) 533
Beanland, R., see Sun 132 (1993) 592
Beaumont, B., see Taylor 132 (1993) 61
Bertram, D., W. Stolz and E.O. Göbel, Direct growth of (AlGa)As/GaAs quantum wires by metalorganic vapour phase epitaxy 132 (1993) 179
Bhat, R., see Caneau 132 (1993) 364
Bierlein, J.D., see Cheng 132 (1993) 280
Bierlein, J.D., see Cheng 132 (1993) 289
Biernath, T., see Erb 132 (1993) 389
Bocchi, C., C. Ferrari, P. Franzosi, A. Bosacchi and S. Franchi, Accurate determination of lattice mismatch in the epitaxial AlAs/GaAs system by high-resolution X-ray diffraction 132 (1993) 427
Bole, V., see Maček 132 (1993) 99
Bogonin, I.A., see Joshkin 132 (1993) 209
Bosacchi, A., see Bocchi 132 (1993) 427
Brandon, S., J.J. Derby, L.J. Atherton, D.H. Roberts and R.L. Vital, Three-dimensional heat transfer effects during the growth of $LiCaAlF_6$ in a modified Bridgman furnace 132 (1993) 261
Brown, P.W., see Graham 132 (1993) 215
Brown, R.A., see Kinney 132 (1993) 551
Bullough, T.J., see Sun 132 (1993) 592

Cai, Q.Y., see Zhang 132 (1993) 200
Calabrese, J., see Cheng 132 (1993) 280
Caneau, C., R. Bhat, C.C. Chang, K. Kash and M.A. Koza, Selective organometallic vapor phase epitaxy of Ga and In compounds: a comparison of TMIn and TEGa versus TMIn and TMGa 132 (1993) 364
Caroli, B., C. Caroli and L. Ramirez-Piscina, Initial front transients in directional solidification of thin samples of dilute alloys 132 (1993) 377
Caroli, C., see Caroli 132 (1993) 377
Catana, A., see Guilloux-Viry 132 (1993) 396
Chang, C.C., see Caneau 132 (1993) 364
Chani, V.I., K. Shimamura, K. Inoue, T. Fukuda and K. Sugiyama, Synthesis and search for equilibrium compositions of borates with the huntite structure 132 (1993) 173
Chani, V.I., K. Inoue, K. Shimamura, K. Sugiyama and T. Fukuda, Segregation coefficients in β-Ga_2O_2 : Cr crystals grown from a Ba_2O_3 based flux 132 (1993) 335
Chebotaev, N.M., see Fischer 132 (1993) 444
Chen, Chuangtian, see Mei 132 (1993) 609
Cheng, H.M., see Zhang 132 (1993) 200
Cheng, L.K., E.M. McCarron III, J. Calabrese, J.D. Bierlein and A.A. Ballman, Development of the nonlinear optical crystal $CsTiOAsO_4$. I. Structural stability 132 (1993) 280
Cheng, L.K., L.T. Cheng, F.C. Zumsteg, J.D. Bierlein and J. Galperin, Development of the nonlinear optical crystal $CsTiOAsO_4$. II. Crystal growth and characterization 132 (1993) 289
Cheng, L.T., see Cheng 132 (1993) 289
Chernov, A.A., S.R. Coriell and B.T. Murray, Morphological stability of a vicinal face induced by step flow 132 (1993) 405
Chin, C.C., T. Morishita and T. Sugimoto, The influence of the surface roughness of the substrates on the surface morphology of $YBa_2Cu_3O_{7-x}$ thin films 132 (1994) 82
Chiu, K., see Shin 132 (1993) 371
Chung, H.T., see Yi 132 (1993) 451
Coleman, C.C. and E. Yamada, Optimization of the vapor reaction growth of single crystal FeI_2 132 (1993) 129
Coriell, S.R., see Chernov 132 (1993) 405

Dabkowska, H.A., see Dabkowski 132 (1993) 205
Dabkowski, A., H.A. Dabkowska and J.E. Greedan, $SrLaGaO_4$ – Czochralski crystal growth and basic properties 132 (1993) 205
Davis, R.W., E.F. Moore and M.R. Zachariah, Numerical modeling of particle dynamics in a rotating disk chemical vapor deposition reactor 132 (1993) 513
Davis, S.H., see Huntley 132 (1993) 141
Demo, P., see Kožíšek 132 (1993) 491
Derby, J.J., see Brandon 132 (1993) 261
Dieker, C., see Bangert 132 (1993) 231

Einset, E.O., K.F. Jensen and C.R. Kleijn, On the origin of return flows in horizontal chemical vapor deposition reactors 132 (1993) 483
Erb, A., T. Biernath and G. Müller-Vogt, $YBa_2Cu_3O_{7-\delta}$–$BaCuO_2$–CuO: investigations on the phase diagram and growth of single crystals. I. The system $BaCuO_2$–CuO_x 132 (1993) 389

Fawcett, P.N., see Zhang 132 (1993) 331
Ferrari, C., see Bocchi 132 (1993) 427
Fischer, K., N.M. Chebotaev and S. Naumov, Isothermal crystal growth of $YBa_2Cu_3O_{7-x}$ in BaO–CuO–$CuO_{0.5}$ flux melts at reduced oxygen partial pressures 132 (1993) 444
Franchi, S., see Bocchi 132 (1993) 427
Franzosi, P., see Bocchi 132 (1993) 427
Freund, L.B., The stress distribution and curvature of a general compositionally graded semiconductor layer 132 (1993) 341
Frye, J.M., see Seki 132 (1993) 25
Fu Peizhen, see Wang 132 (1993) 329
Fukuda, T., see Chani 132 (1993) 173
Fukuda, T., see Chani 132 (1993) 335
Fukuda, T., see Matsumoto 132 (1993) 348
Füredi-Milhofer, H., see Komunjer 132 (1993) 122

Galperin, J., see Cheng 132 (1993) 289
Galtier, P., see Mathet 132 (1993) 241
Ge, C.Z., see Zhang 132 (1993) 200
Gedridge, Jr., R.W., see Shin 132 (1993) 371
Gibbins, C.J., see Bangert 132 (1993) 231
Gill, W.N., see Lee 132 (1993) 226
Glass, R.C., L.O. Kjellberg, V.F. Tsvetkov, J.E. Sundgren and E. Janzén, Structural macro-defects in 6H-SiC wafers 132 (1993) 504
Göbel, E.O., see Bertram 132 (199? 179
Goodhew, P.J., see Sun 132 (199. 592
Graham, S. and P.W. Brown, The low temperature formation of octacalcium phosphate 132 (1993) 215
Greedan, J.E., see Dabkowski 132 (1993) 205
Guergouri, K. and R. Triboulet, Determination of the PbTe–MnTe pseudo-binary phase diagram on the Pb-rich side 132 (1993) 20
Guilloux-Viry, M., C. Thivet, A. Perrin, M. Sergent, M.G. Karkut, Crystal growth of (110) and (103) $YBa_2Cu_3O_7$ thin films in-situ deposited by laser ablation on (110) $SrTiO_3$ single-crystal substrates 132 (1993) 396
Gusev, G.M., see Lubyshev 132 (1993) 533

Haga, T., M. Ohishi, K. Imai, K. Kumazaki, K. Ohmori, H. Saito and Y. Abe, Characterization by ion-channeling of ZnSe grown by photo-assisted molecular beam epitaxy 132 (1993) 575
Halpern, J.B., see Seki 132 (1993) 25
Harvey, A.J., see Bangert 132 (1993) 231
He, Changzhen, see Mei 132 (1993) 609
Herberholz, R., see Taylor 132 (1993) 61
Hirai, T., see Zhang 132 (1993) 337
Hoshikawa, K., see Matsumoto 132 (1993) 348
Hsieh, J.Y., see Hwang 132 (1993) 523
Hu, Z.W., see Zhang 132 (1993) 200
Hubík, P., see Šestáková 132 (1993) 345
Huntley, D.A. and S.H. Davis, Thermal effects in rapid directional solidification: weakly-nonlinear analysis of oscillatory instabilities 132 (1993) 141
Hurle, D.T.J., see Joyce 132 (1993) 1
Hwang, C.C., C.S. Wu and J.Y. Hsieh, The effect of curved interface shape on thermal stress during Czochralski crystal growth 132 (1993) 523

Imai, K., see Haga 132 (1993) 575
Inoue, K., see Chani 132 (1993) 173
Inoue, K., see Chani 132 (1993) 335

Jang, D.-H., see Yoo 132 (1993) 43
Janzén, E., see Glass 132 (1993) 504
Jensen, K.F., see Einset 132 (1993) 483
Jiang, S.S., see Zhang 132 (1993) 200
Jiang, Z.K., see Soga 132 (1993) 414
Jimbo, T., see Soga 132 (1993) 134
Jimbo, T., see Soga 132 (1993) 414
Joshkin, V.A., S.R. Oktyabrsky, I.A. Bogonin and A.A. Orlikovsky, Low temperature preannealing for carbon removal from Si surface in GaAs-on-Si molecular beam epitaxial growth 132 (1993) 209
Jowett, J.M., see Bangert 132 (1993) 231
Joyce, B.A., see Zhang 132 (1993) 331
Joyce, G.C., D.T.J. Hurle and Q.A.E. Vaughan, Novel development of the weighing method for automatic Czochralski crystal growth of semiconductors 132 (1993) 1
Joyce, T.B.F., see Sun 132 (1993) 592

Kanakavel, M., see Narayana Kalkura 132 (1993) 617
Kaneyama, T., see Liliental-Weber 132 (1993) 103
Karkut, M.G., see Guilloux-Viry 132 (1993) 396
Kash, K., see Caneau 132 (1993) 364
Kedar, E., see Weiss 132 (1993) 191
Kida, M., see Ono 132 (1993) 297
Kim, H.-M., see Yoo 132 (1993) 43
Kim, J.-S., see Yoo 132 (1993) 43
Kinney, T.A. and R.A. Brown, Application of turbulence modeling to the integrated hydrodynamic thermal-capillary model of Czochralski crystal growth of silicon 132 (1993) 551
Kitamura, M., see Sasaki 132 (1993) 435
Kjellberg, L.O., see Glass 132 (1993) 504
Kleijn, C.R., see Einset 132 (1993) 483
Klimovitsky, I.K., Calculation of the growth velocity for liquid encapsulated Czochralski grown GaAs crystals 132 (1993) 614
Koak, B.-H., see Yoo 132 (1993) 43
Komunjer, Lj., M. Marković and H. Füredi-Milhofer, Influence of amino acids on the precipitation kinetics of calcium oxalate monohydrate 132 (1993) 122
Kondo, S., S. Matsumoto and H. Nagai, Metalorganic chloride vapor phase epitaxial growth of III-V compounds in a single reactor 132 (1993) 305
Kou, S., see Lin 132 (1993) 461
Kou, S., see Lin 132 (1993) 467
Kou, S., see Lan 132 (1993) 471
Kou, S., see Lan 132 (1993) 578
Koza, M.A., see Caneau 132 (1993) 364
Kožíšek, Z. and P. Demo, Transient kinetics of binary nucleation 132 (1993) 491
Krištofik, J., see Šestáková 132 (1993) 345
Kühne, H. and H. Richter, Control of $Si_{1-x}Ge_x$ growth from the gas phase. I. The effect of the layer source gases (E) 132 (1993) 357
Kumashiro, Y., Y. Okada and H. Okumura, Isotope effects on boron phosphide single-crystal wafers 132 (1993) 611
Kumazaki, K., see Haga 132 (1993) 575

Lan, C.W. and S. Kou, Formulation for correcting optical distortions due to a transparent floating zone 132 (1993) 471
Lan, C.W. and S. Kou, Radial dopant segregation in zero-gravity floating crystal growth 132 (1993) 578
Lee, H.W., see Yi 132 (1993) 451
Lee, Y.-T., see Yoo 132 (1993) 43
Lee, Y.W., R. Ananth and W.N. Gill, Selection of a length scale in unconstrained dendritic growth with convection in the melt 132 (1993) 226
Li, S.H., see Zhang 132 (1993) 200
Liliental-Weber, Z., T. Kaneyama, M. Terauchi and M. Tanaka, Application of convergent-beam illumination methods to the study of lattice distortion across the interface 132 (1993) 103
Lin, M.H. and S. Kou, Dopant segregation control in Czochralski crystal growth with a wetted float 132 (1993) 461
Lin, M.H. and S. Kou, Crystal pulling with floating wetted shapers 132 (1993) 467
Ling, D.L., see Zhang 132 (1993) 200
Lubyshev, D.I., J.C. Rossi, G.M. Gusev and P. Basmaji, Nano-scale wires of GaAs on porous Si grown by molecular beam epitaxy 132 (1993) 533

Maček, J., S. Zakrajšek, J. Radkovič and V. Bole, Crystallization of gypsum from batch chemical neutralizations 132 (1993) 99
Mainzer, N., see Weiss 132 (1993) 191
Marković, M., see Komunjer 132 (1993) 122
Mathet, V., P. Galtier, F. Nguyen-Van-Dau, G. Padeletti and J. Olivier, A microstructural study of crystalline defects in $PbSe/BaF_2/CaF_2$ on (111) Si grown by molecular beam epitaxy 132 (1993) 241
Matsumoto, F., Y. Okano, I. Yonenaga, K. Hoshikawa and T. Fukuda, Growth of twin-free ⟨100⟩ InP single crystals by the liquid encapsulated vertical Bridgman technique 132 (1993) 348
Matsumoto, S., see Kondo 132 (1993) 305
McCarron III, E.M., see Cheng 132 (1993) 280
Mei, Linfeng, Changzhen He and Chuangtian Chen, Flux growth of $KBe_2BO_3F_2$ 132 (1993) 609
Mil'vidskii, M.G., see Vdovin 132 (1993) 477
Ming, N.B., see Zhang 132 (1993) 200
Mito, I., see Sasaki 132 (1993) 435
Moiseev, I.I., see Volkov 132 (1993) 359
Möller, J., see Slezov 132 (1993) 419
Moore, E.F., see Davis 132 (1993) 513
Mori, M., see Soga 132 (1993) 134
Mori, M., see Soga 132 (1993) 414
Morishita, T., see Chin 132 (1993) 82
Müller-Vogt, G., see Erb 132 (1993) 389
Murray, B.T., see Chernov 132 (1993) 405

Nagai, H., see Kondo 132 (1993) 305
Narayana Kalkura, S., V.K. Vaidyan, M. Kanakavel and P. Ramasamy, Crystallization of uric acid 132 (1993) 617
Naumov, S., see Fischer 132 (1993) 444
Neave, J.H., see Zhang 132 (1993) 331
Nelson, J., Heat conduction problems in crystal growth from the vapor 132 (1993) 538
Nguyen-Van-Dau, F., see Mathet 132 (1993) 241
Nishida, I., see Arita 132 (1993) 71

Nishida, T., H. Suriura, M. Notomi and T. Tamamura, InGaAs/InP quantum wires selectively grown by chemical beam epitaxy 132 (1993) 91
Notomi, M., see Nishida 132 (1993) 91

Oh, D.-K., see Yoo 132 (1993) 43
Ohishi, M., see Haga 132 (1993) 575
Ohmori, K., see Haga 132 (1993) 575
Okabe, H., see Seki 132 (1993) 25
Okada, Y., see Kumashiro 132 (1993) 611
Okano, Y., see Matsumoto 132 (1993) 348
Okazaki, M., see Wada 132 (1993) 115
Oktyabrsky, S.R., see Joshkin 132 (1993) 209
Okumura, M., see Kumashiro 132 (1993) 611
Olivier, J., see Mathet 132 (1993) 241
Ono, N., M. Kida, Y. Arai and K. Sahira, A numerical study of the influence of feeding polycrystalline silicon granules on melt temperature in the continuous Czochralski process 132 (1993) 297
Orlikovsky, A.A., see Joshkin 132 (1993) 209

Padeletti, G., see Mathet 132 (1993) 241
Partanen, J., see Prieur 132 (1993) 599
Pashley, D.W., see Zhang 132 (1993) 331
Perrin, A., see Guilloux-Viry 132 (1993) 396
Perrin, S.D., see Bangert 132 (1993) 231
Prieur, E., T. Tuomi, J. Partanen, E. Yli-Juuti and M. Tilli, Synchrotron topographic study of defects in liquid-encapsulated Czochralski-grown semi-insulating gallium arsenide wafers 132 (1993) 599

Radkovič, J., see Maček 132 (1993) 99
Ramasamy, P., see Narayana Kalkura 132 (1993) 617
Ramirez-Piscina, L., see Caroli 132 (1993) 377
Regel, L.L, see Shen 132 (1993) 250
Regel, L.L, see Shen 132 (1993) 351
Richter, H., see Kühne 132 (1993) 357
Roberts, D.H., see Brandon 132 (1993) 261
Rossel, C., see Guilloux-Viry 132 (1993) 396
Rossi, J.C., see Lubyshev 132 (1993) 533

Sahira, K., see Ono 132 (1993) 297
Saito, H., see Haga 132 (1993) 575
Saitoh, M., see Yamada 132 (1993) 48
Sasaki, M., see Zhang 132 (1993) 337
Sasaki, T., M. Kitamura and I. Mito, Selective metalorganic vapor phase epitaxial growth of InGaAsP/InP layers with bandgap energy control in InGaAs/InGaAsP multiple-quantum well structures 132 (1993) 435
Schanz, U., see Yu 132 (1993) 606
Schmelzer, J., see Slezov 132 (1993) 419
Schmidbauer, E., see Yu 132 (1993) 606
Seki, K., J.M. Frye, H. Okabe and J.B. Halpern, Laser-induced chemical vapor deposition of aluminum from trimethylaluminum: wavelength and temperature dependence 132 (1993) 25
Sergent, M., see Guilloux-Viry 132 (1993) 396
Šestáková, V., P. Hubík, B. Štěpánek and J. Krištofik, GaSb single crystals doped with manganese 132 (1993) 345
Shen, J., D.K. Aidun, L.L. Regel and W.R. Wilcox, Characterization of precipitates in CdTe and $Cd_{1-x}Zn_xTe$ grown by vertical Bridgman–Stockbarger technique 132 (1993) 250
Shen, J., D.K. Aidun, L.L. Regel and W.R. Wilcox, Etch pits originating from precipitates in CdTe and $Cd_{1-x}Zn_xTe$ grown by the vertical Bridgman–Stockbarger method 132 (1993) 351
Shimamura, K., see Chani 132 (1993) 173
Shimamura, K., see Chani 132 (1993) 335
Shin, J., K. Chiu, G.B. Stringfellow and R.W. Gedridge, Jr., Diisopropylantimonyhydride (DIPSbH) for low temperature epitaxial growth of InSb 132 (1993) 371
Slezov, V.V., J. Schmelzer and J. Möller, Ostwald ripening in porous materials 132 (1993) 419
Smith, A.D., see Bangert 132 (1993) 231
Soga, T., T. Suzuki, M. Mori, T. Jimbo and M. Umeno, The effects of the growth parameters on the initial stage of epitaxial growth of GaP on Si by metalorganic chemical vapor deposition 132 (1993) 134
Soga, T., T. Suzuki, M. Mori, Z.K. Jiang, T. Jimbo and M. Umeno, Electrical properties of GaP on Si grown by metalorganic chemical vapor deposition 132 (1993) 414
Someno, Y., see Zhang 132 (1993) 337
Štěpánek, B., see Šestáková 132 (1993) 345
Stolz, W., see Bertram 132 (1993) 179
Stringfellow, G.B., see Shin 132 (1993) 371
Sugimoto, T., see Chin 132 (1993) 82
Sugiyama, K., see Chani 132 (1993) 173
Sugiyama, K., see Chani 132 (1993) 335
Sun, D. and E. Towe, Molecular beam epitaxial growth of (Al,Ga)As/GaAs heterostructures and Si doping characterization study on vicinal (110) GaAs substrates 132 (1993) 166
Sun, D., R. Beanland, T.B.F. Joyce, J.V. Armstrong, T.J. Bullough and P.J. Goodhew, Orientations and morphology of Al layers grown on GaAs by chemical beam epitaxy 132 (1993) 592
Sundgren, J.E., see Glass 132 (1993) 504
Suriura, H., see Nishida 132 (1993) 91
Suzuki, N., see Arita 132 (1993) 71
Suzuki, T., see Soga 132 (1993) 134
Suzuki, T., see Soga 132 (1993) 414

Tachikawa, S., see Wada 132 (1993) 115
Tamada, H., see Yamada 132 (1993) 48
Tamamura, T., see Nishida 132 (1993) 91
Tanaka, M., see Liliental-Weber 132 (1993) 103
Taylor, S.J., B. Beaumont and R. Herberholz, Carbon doping of $Ga_xIn_{1-x}As$ by atmospheric pressure organometallic vapour phase epitaxy 132 (1993) 61
Terauchi, M., see Liliental-Weber 132 (1993) 103
Thivet, C., see Guilloux-Viry 132 (1993) 396
Tilli, M., see Prieur 132 (1993) 599
Towe, E., see Sun 132 (1993) 166
Triboulet, R., see Guergouri 132 (1993) 20
Tsvetkov, V.F., see Glass 132 (1993) 504
Tuomi, T., see Prieur 132 (1993) 599

Ueltzen, M., The Verneuil flame fusion process: substances 132 (1993) 315
Umeno, M., see Soga 132 (1993) 134
Umeno, M., see Soga 132 (1993) 414

Vaidyan, V.K., see Narayana Kalkura 132 (1993) 617
Van Tendeloo, G., see Volkov 132 (1993) 359
Vargaftik, M.N., see Volkov 132 (1993) 359
Vaughan, Q.A.E., see Joyce 132 (1993) 1
Vdovin, V.I., M.G. Mil'vidskii and T.G. Yugova, Antiphase boundaries in GaAs layers on Si and Ge 132 (1993) 477
Vital, R.L., see Brandon 132 (1993) 261
Volkov, V.V., G. Van Tendeloo, M.N. Vargaftik and I.I. Moiseev, High-resolution electron microscopy observations of large Pd clusters 132 (1993) 359

Wada, N., M. Okazaki and S. Tachikawa, Effects of calcium-binding polysaccharides from calcareous algae on calcium carbonate polymorphs under conditions of double diffusion 132 (1993) 115
Walker, J.S., and M.G. Williams, Effects of the crystal's non-zero electrical conductivity on the rotationally driven melt motion during Czochralski silicon growth with a uniform, transverse magnetic field 132 (1993) 31
Wang Junxin, Fu Peizhen and Wu Yicheng, Growth and characterization of $Pb_xSr_{1-x}B_4O_7$ solid solution crystals 132 (1993) 329
Wang, S.J., see Zhang 132 (1993) 200
Weiss, E., E. Kedar and N. Mainzer, The formation of twins in ⟨111⟩ HgCdTe grown by traveling heater method and their effect on device quality 132 (1993) 191
Wilcox, W.R., see Shen 132 (1993) 250
Wilcox, W.R., see Shen 132 (1993) 351
Wilkinson, V.A., see Bangert 132 (1993) 231
Williams, M.G., see Walker 132 (1993) 31
Wu, C.S., see Hwang 132 (1993) 523
Wu Yicheng, see Wang 132 (1993) 329

Yamada, A., H. Tamada and M. Saitoh, Liquid phase epitaxial growth of $LiNbO_3$ thin film using Li_2O–B_2O_3 flux system 132 (1993) 48
Yamada, E., see Coleman 132 (1993) 129
Yi, K.W., H.T. Chung, H.W. Lee and J.K. Yoon, The effects of pulling rates on the shape of crystal/melt interface in Si single crystal growth by the Czochralski method 132 (1993) 451
Yli-Juuti, E., see Prieur 132 (1993) 599
Yonenaga, I., see Matsumoto 132 (1993) 348
Yoo, J.-B., J.-S. Kim, D.-H. Jang, B.-H. Koak, D.-K. Oh, H.-M. Kim and Y.-T. Lee, Effects of the V/III ratio on Si doping in InGaAs lattice-matched to InP grown by organometallic vapor phase epitaxy 132 (1993) 43
Yoon, J.K., see Yi 132 (1993) 451
Yu, F., U. Schanz and E. Schmidbauer, Single crystal growth of $FeWO_4$ and $CuWO_4$ 132 (1993) 606
Yugova, T.G., see Vdovin 132 (1993) 477

Zachariah, M.R., see Davis 132 (1993) 513
Zakrajšek, S., see Maček 132 (1993) 99
Zhang, J., see Zhang 132 (1993) 331
Zhang, W., Y. Someno, M. Sasaki and T. Hirai, Heteroepitaxy of AlN on α-Al_2O_3 by electron cyclotron resonance plasma-assisted chemical vapor deposition at low temperatures 132 (1993) 337
Zhang, X., D.W. Pashley, J.H. Neave, P.N. Fawcett, J. Zhang and B.A. Joyce, Reflection high-energy electron diffraction/transmission electron microscopy observation of growth of InAs on GaAs (110) by molecular beam epitaxy 132 (1993) 331
Zhang, Z.M., H.M. Cheng, S.H. Li, Q.Y. Cai, D.L. Ling, S.J. Wang, Z.W. Hu, S.S. Jiang, C.Z. Ge and N.B. Ming, Morphologic study of (100) single crystal diamond films epitaxially grown by chemical vapor deposition 132 (1993) 200
Zumsteg, F.C., see Cheng 132 (1993) 289

Journal of Crystal Growth 132 (1993) 626–628
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index

Aluminum 25, 592
– arsenide 427
– gallium arsenide 166, 179
– oxide 337
Apparatus
– for melt growth
– – by Czochralski method
– – – automatic diameter control 1
– – – segregation control 461
– – – shaped crystal pulling 467

Barium
– cuprate 389
– fluoride 241
Borates 173
Boron
– phosphide 611

Cadmium
– telluride 250, 351
– zinc telluride 250, 351
Calcium
– carbonate 115
– fluoride 241
– oxalate monohydrate 122
– phosphate 215
Cesium
– titanyl arsenate 280, 289
Clusters
– formation in binary systems 491
– of metals 359
Computer simulation
– of dopant concentration
– – in floating zone method 578
– of flow
– – in CVD reactor 483, 513
– – in Czochralski method 551
– of oxygen concentration
– – in Czochralski method 451
– of solidification interface
– – in Czochralski method 451
– of temperature fields
– – in Bridgman method 261
– – in Czochralski method 297, 451, 551
– – in floating zone method 578
Constitutional supercooling
– theory of 405

Convection 226, 483
Copper
– tungstate 606

Dendritic growth
– of iron iodide 129
– of succinonitrile 226
Device characterization
– diodes 191
– electronic materials 191, 504
– heterojunction 341
– heterostructures 166, 427, 435
– lasers 289
– quantum wells 231, 435
– quantum wires 91, 179
Diamond 200
Diffusional control
– of clusters 419
Diodes, see Device characterization

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– chemical 179, 241, 250

Gallium
– antimonide 345
– arsenide 103, 166, 179, 209, 331, 364, 427, 477, 533, 599, 614
– indium arsenide 43, 61, 91, 231, 364, 435
– indium arsenide phosphide 231, 435
– indium phosphide 364
– oxide 335
– phosphide 134, 364, 414
Gypsum 99

Heat flow control
– in Czochralski method 297
– in vapor growth method 538
Heterojunction, see Device characterization
Hydrodynamics, see Convection

Indium
– antimonide 371
– arsenide 331, 364
– gallium phosphide 231
– phosphide 91, 231, 348, 364, 435
Iron
– iodide 129
– tungstate 606

Kinetics
- of desupersaturation 99
- of dissolution 419
- of growth 25, 99, 122, 215, 405, 419, 533, 538, 614
- of nucleation 115, 134, 141, 491
- of silicon incorporation in indium gallium arsenide 43

Lasers, see Device characterization
Lasers, crystals for 261, 435
Lead
- fluoride 241
- strontium borate 329
- telluride/manganese telluride alloys 20
Lithium
- calcium aluminum fluoride 261
- niobate 48

Melt growth technique
- by Bridgman–Stockbarger method
- - of cadmium telluride 250, 351
- - of cadmium zinc telluride 250, 351
- - of indium phosphide 348
- - of lead telluride/manganese telluride alloys 20
- - of lithium calcium aluminum fluoride 261
- by Czochralski method
- - of gallium antimonide 345
- - of gallium arsenide 599, 614
- - of silicon 31, 451
- - of sodium nitrate 461, 467
- - of strontium lanthanum gallium oxide 205
- - theory of 1, 31, 297, 523, 551, 614
- by floating zone method
- - of sodium nitrate 467
- - theory of 467, 578
- by Kyropoulos method
- - of lead strontium borate 329
- by traveling heater method
- - of mercury cadmium telluride 191
- by Verneuil method
- - review of 315
- theory of 141
Mercury
- cadmium telluride 191
Metal
- clusters 359
Microgravity, growth under
- theory of 377, 578
Morphological stability
- of calcium carbonate 115
- of succinonitrile 226
- theory of 141, 405, 538

Nucleation
- of aluminum 592
- of binary systems 491
- of palladium clusters 359
Numbers
- Biot 523
- Grashof 451, 483
- Rayleigh 451
- Reynolds 483

Palladium
- clusters 359
Phase diagrams
- of barium oxide/copper(II) oxide/copper(I) oxide 444
- of lead telluride/manganese telluride 20
Potassium
- beryllium borate fluoride 609
Precursor
- for indium antimonide 371

Semiconductors (III–V) 305
Silicon 31, 451
- carbide 504
Sodium
- nitrate 461, 467
Solid growth technique
- by recrystallization
- - of copper tungstate 606
- - of iron tungstate 606
Solution growth technique
- by flux method
- - of borates 173
- - of cesium titanyl arsenate 280, 289
- - of gallium oxide 335
- - of potassium beryllium borate fluoride 609
- - of yttrium barium cuprate 444
- by gel method
- - of calcium carbonate 115
- - of uric acid 617
- by low temperature method
- - of calcium oxalate 122
- - of gypsum 99
- - of octacalcium phosphate 215
- theory of 405
Stefan problem or moving boundary problem
- theory of 551, 578
Strontium
- lantanum gallium oxide 205
Succinonitrile 226
Superconductivity materials, high T_c
- bulk
- - of YBCO 82, 396, 444
Superlattices, multilayers
- of III–V compounds 341, 435
Surface morphology
- of yttrium barium cuprate 82
Surface structure
- of yttrium barium cuprate 396
Thin film growth, epitaxy
- by laser ablation
- - of yttrium barium cuprate 396

– by liquid phase epitaxy
– – of lithium niobate 48
– by metalorganic molecular beam epitaxy
– – of aluminum 592
– – of gallium indium arsenide 91
– – of indium phosphide 91
– by molecular beam epitaxy
– – of aluminum arsenide 427
– – of aluminum gallium arsenide 166
– – of barium fluoride 241
– – of calcium fluoride 241
– – of gallium arsenide 103, 209, 331, 427, 533
– – of indium arsenide 331
– – of lead fluoride 241
– by molecular beam epitaxy, photo-assisted
– – of zinc selenide 575
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of boron phosphide 611
– – – of diamond 200
– – – theory of 483, 513
– – through chemical vapor deposition, plasma-assisted
– – – of aluminum oxide 337
– – through evaporation and condensation
– – – of yttrium barium cuprate 82
– – through metalorganic chemical vapor deposition
– – – of aluminum 25
– – – of aluninum gallium arsenide 179
– – – of gallium arsenide 179, 364, 477
– – – of gallium indium arsenide 43, 61, 231, 364, 435
– – – of gallium indium arsenide phosphide 231, 435
– – – of gallium indium phosphide 364
– – – of gallium phosphide 134, 354, 414
– – – of indium antimonide 371
– – – of indium phosphide 231, 364, 435
– – – of semiconductors (III–V) 305
– – – theory of 364

Uric acid 617

Vapor growth technique
– by chemical transport
– – of copper tungstate 606
– – of iron iodide 129
– – of iron tungstate 606
– by evaporation and condensation
– – of silicon carbide 504
– – of succinonitrile 226
– – of ytterbium 71
– – of ytterbium oxide 71
– – theory of 538

Ytterbium 71
– oxide 71
Yttrium
– barium cuprate 82, 396, 444

Zinc
– selenide 575